

Amendments to the Claims:

1. (Original) A semiconductor device comprising:
a Schottky layer; and
a Schottky electrode that is formed on the Schottky layer and has a Schottky contact with the Schottky layer, wherein the Schottky layer is composed of a compound semiconductor including In and P, and the portion of the Schottky electrode that touches the Schottky layer is composed of material whose main constituents are La and B.
2. (Original) The semiconductor device according to claim 1, wherein the Schottky layer is composed of one of InGaP, InP and InAlGaP.
3. (Original) The semiconductor device according to claim 2, wherein the portion of the Schottky electrode that touches the Schottky layer is composed of LaB₆.
4. (Original) The semiconductor device according to claim 3, wherein the semiconductor device is a transistor or a diode.
5. (Original) The semiconductor device according to claim 1, wherein the portion of the Schottky electrode that touches the Schottky layer is composed of LaB₆.
6. (Original) The semiconductor device according to claim 1, wherein the semiconductor device is a transistor or a diode.

Claims 7-12 (Cancelled).